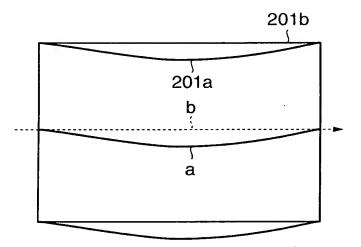
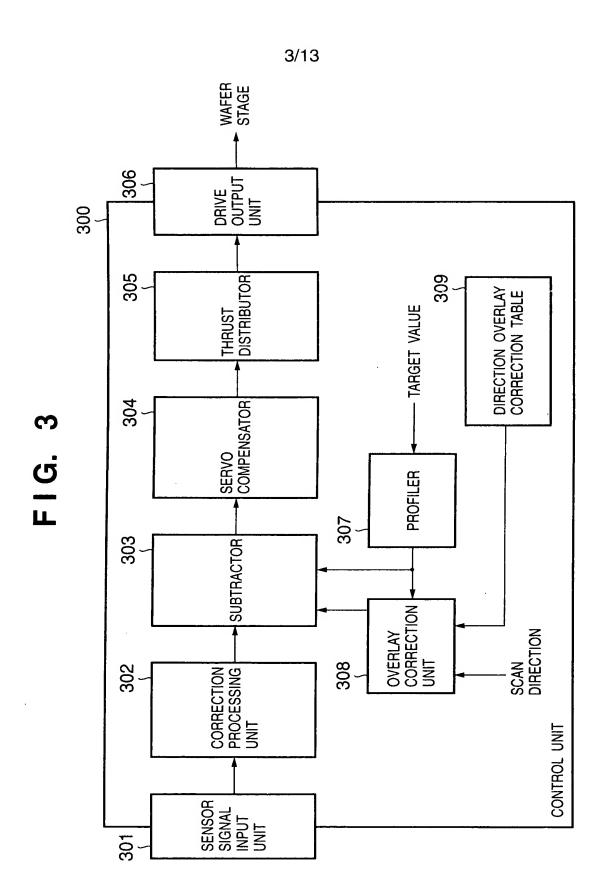


FIG. 2

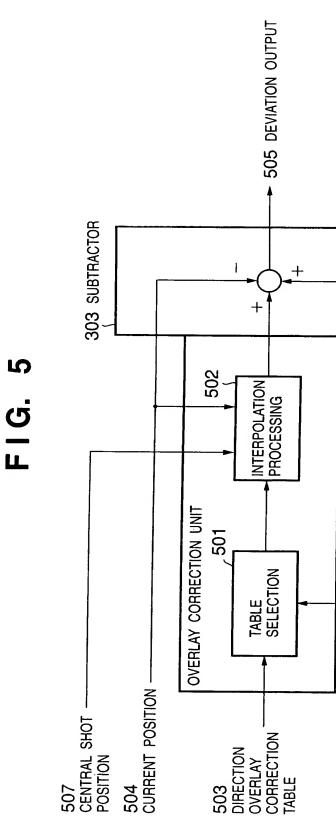




ŝ 3 θ INTERFERENCE CORRECTION (ABBE) 417 INTER-AXIAL ωx". ωγ". θ, <u>^</u> MAGNIFICATION 416a MAGNIFICATION CORRECTION 416b b, ,× × ε, , **^** 415 **1/L**q 414a 414b FIG. 414c 413 412b COORDINATE TRANSFORMATION COORDINATE TRANSFORMATION 411 MIRROR SURFACE REFORMATION 412a 410a ENVIRONMENTAL CORRECTION ENVIRONMENTAL CORRECTION 410b Ξ 22 召 ដ Ш \simeq പ്പ ニ 403~ 407~ 404~ 405~ 406~ 408~ 402~ 409~

4/13

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5/13

508 PROFILE

308

506 SCAN DIRECTION

TOCSOSBI LOTIBOR

FIG. 6

ORIGIN INTERVAL		-16.000 4.000			
CORRECTION DATA (FORWARD)		[nm/ppb]			
X 5 4 2 1 -1 -4 -3 -6 -12	Y 1 1 0 -1 -4 -2 -4 -5 -9	Z 10 8 10 12 13 10 7 4	Qx 0 10 20 20 20 40 10 0	Qy - 10 - 10 20 40 30 40 50 80 60	Qz 20 10 10 10 0 -10 -30 -30 -40
(REVERSE) X 4 2 0 0 -3 -5 -5 -7 -14	Y 0 0 -1 -1 -4 -3 -4 -5 -9	Z 9 6 11 10 9 6 4 -1	Qx 10 0 10 20 40 20 20 10	Qy -10 0 10 30 10 40 60 100 80	Qz 20 10 10 20 0 -10 -30 -30

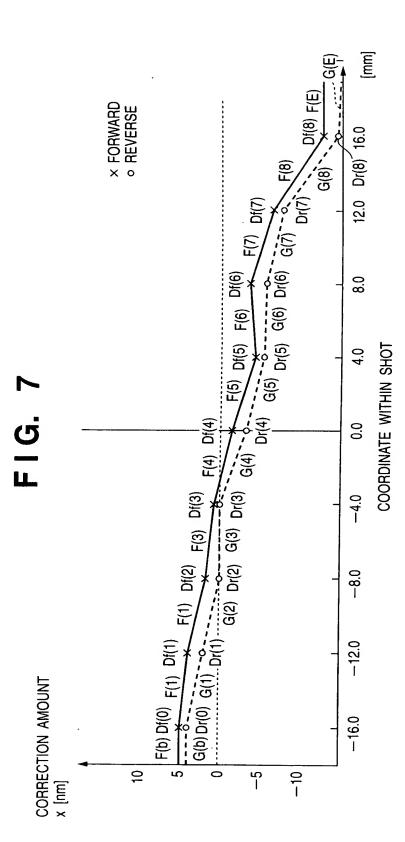
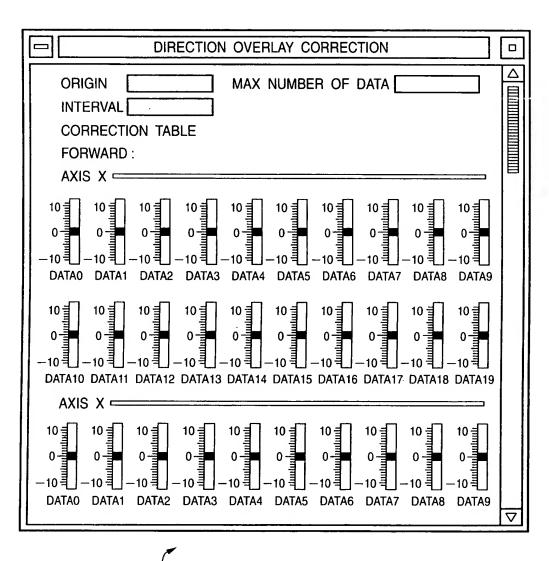
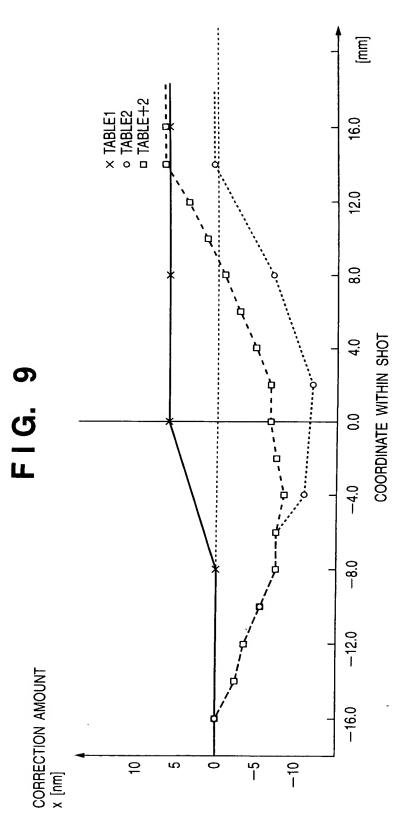


FIG. 8



1001



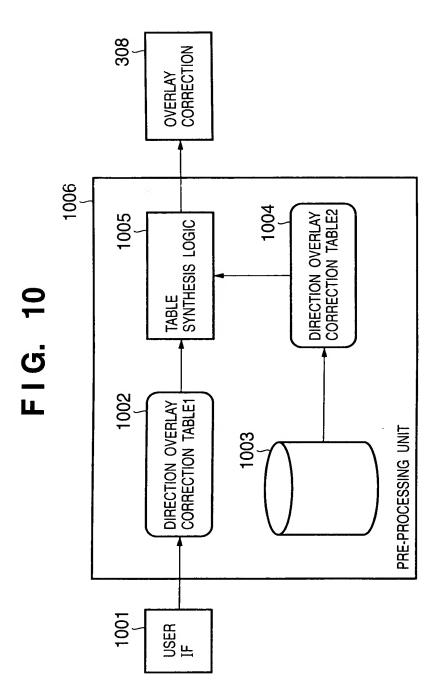
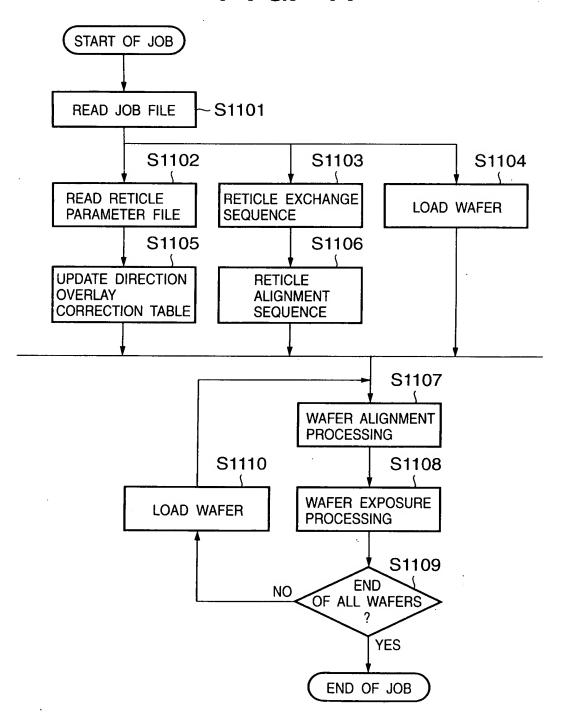
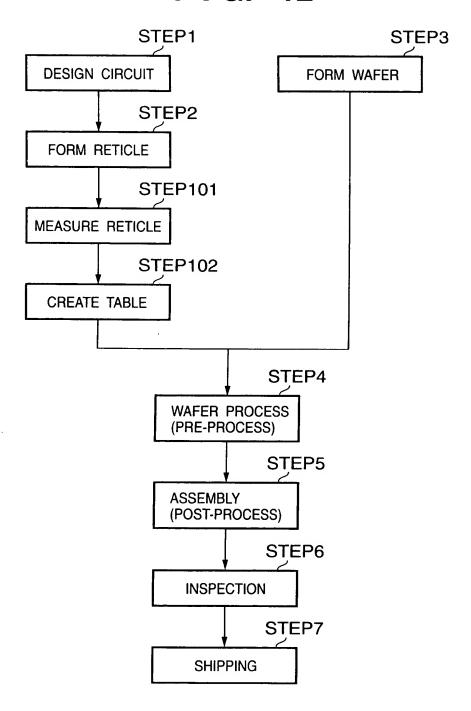


FIG. 11



12/13

FIG. 12



SEMICONDUCTOR DEVICE MANUFACTURING FLOW

FIG. 13

